

In the Specification:

After the title, please insert the sentence: --This is a continuation of application

q1

Serial No. 09/239,617 filed January 29, 1999--

In the Claims:

Please cancel claims 1-90.

Please add the following new claims:

q2 --91. An integrated module comprising:

a single interconnect substrate;

a first active circuit chip wire bonded to said single interconnect substrate;

a first discrete component surface mounted on said single interconnect substrate;

and

a second discrete component embedded in said single interconnect substrate.--

--92. The integrated module of claim 91 wherein said first discrete component is surface mounted using a high-temperature solder.--

--93. The integrated module of claim 91 further comprising a solder mask area on said single interconnect substrate.--

--94. The integrated module of claim 93 wherein said solder mask area is adjacent to said first discrete component.--

--95. The integrated module of claim 91 wherein said first discrete component is selected from the group consisting of an inductor, a transformer, a capacitor, and a resistor.--

--96. The integrated module of claim 91 wherein said second discrete component is selected from the group consisting of an inductor, a transformer, a capacitor, and a resistor.--

--97. The integrated module of claim 91 wherein said single interconnect substrate comprises a plurality of metal layers and a plurality of dielectric layers.--

--98. The integrated module of claim 97 wherein at least one of said plurality of metal layers defines a printed component.--

--99. The integrated module of claim 98 wherein said printed component is selected from the group consisting of an inductor, a resistor, a capacitor, and a transformer.--

--100. The integrated module of claim 97 wherein at least one of said plurality of metal layers defines a ground plane.--

--101. The integrated module of claim 91 wherein said first active circuit chip comprises an RF section.--

--102. The integrated module of claim 91 wherein said first active circuit chip comprises an IF section.--

--103. The integrated module of claim 91 further comprising a second active circuit chip.--

--104. The integrated module of claim 103 wherein said first and second active circuit chips respectively comprise first and second RF sections.--

--105. The integrated module of claim 103 wherein said first active circuit chip comprises an RF section and wherein said second active circuit chip comprises an IF section.--

--106. The integrated module of claim 103 wherein said first active circuit chip comprises a CMOS chip and wherein said second active circuit chip comprises a GaAs chip.--

--107. The integrated module of claim 97 wherein at least one of said plurality of metal layers defines said first discrete component.--

--108. The integrated module of claim 107 wherein said first discrete component is selected from the group consisting of an inductor, a resistor, a capacitor, and a transformer.--

--109. The integrated module of claim 97 wherein at least one of said plurality of metal layers defines said second discrete component.--

--110. The integrated module of claim 109 wherein said second discrete component is selected from the group consisting of an inductor, a resistor, a capacitor, and a transformer.--

--111. An integrated module comprising:
a single interconnect substrate including a plurality of metal layers and a plurality of dielectric layers;

first and second active circuit chips on a top surface of said single interconnect substrate;

a conductive ring formed on said single interconnect substrate, said conductive ring enclosing said first and second active circuit chips;

a conductive strip formed on said single interconnect substrate, said conductive strip situated between said first and second active circuit chips;

a metal lid covering said first and second active circuit chips, said metal lid contacting said conductive ring and said conductive strip, wherein said metal lid, said

conductive ring, and said conductive strip substantially prevent electromagnetic interference from reaching said first and second active circuit chips.--

--112. The integrated module of claim 111 further comprising a first ground plane below said first active circuit chip, wherein said first ground plane substantially prevents electromagnetic interference from reaching said first active circuit chip.--

--113. The integrated module of claim 112 wherein said first ground plane is defined by at least one of said plurality of metal layers below said first active circuit chip.--

--114. The integrated module of claim 112 further comprising a second ground plane below said second active circuit chip, wherein said second ground plane substantially prevents electromagnetic interference from reaching said second active circuit chip.--

--115. The integrated module of claim 114 wherein said second ground plane is defined by at least one of said plurality of metal layers below said second active circuit chip.--

--116. The integrated module of claim 111 wherein said conductive ring is coupled to ground through a plurality of peripheral vias.--

--117. The integrated module of claim 112 wherein said conductive ring is coupled to said first ground plane through a plurality of peripheral vias.--

--118. The integrated module of claim 114 wherein said conductive ring is coupled to said second ground plane through a plurality of peripheral vias.--

--119. The integrated module of claim 111 wherein said conductive strip is coupled to ground through a plurality of peripheral vias.--

PROPRIETARY INFORMATION